

## CORRECTION

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# Correction: Controlling barrier height and spectral responsivity of p–i–n based GeSn photodetectors via arsenic incorporation

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Correction for 'Controlling barrier height and spectral responsivity of p–i–n based GeSn photodetectors via arsenic incorporation' by Mohamed A. Nawwar *et al.*, *RSC Adv.*, 2023, **13**, 9154–9167, <https://doi.org/10.1039/D3RA00805C>.

The authors regret that the author associations with affiliations were incorrectly shown in the original manuscript. The corrected list of affiliations is as shown above.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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